

BDX33/A/B/C

Power Linear and Switching Applications

- High Gain General Purpose
- Power Darlington TR
- Complement to BDX34/34A/34B/34C respectively



1.Base 2.Collector 3.Emitter

NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings $T_C=25^{\circ}C$ unless otherwise noted

| Symbol | Parameter | Value | Units |
|------------------|--|------------|-------|
| V_{CBO} | Collector-Base Voltage | | |
| CDC | : BDX33 | 45 | V |
| | : BDX33A | 60 | V |
| | : BDX33B | 80 | V |
| | : BDX33C | 100 | V |
| V _{CEO} | Collector-Emitter Voltage | | |
| | : BDX33 | 45 | V |
| | : BDX33A | 60 | V |
| | : BDX33B | 80 | V |
| | : BDX33C | 100 | V |
| I _C | Collector Current (DC) | 10 | А |
| СР | *Collector Current (Pulse) | 15 | А |
| l _B | Base Current | 0.25 | А |
| P _C | Collector Dissipation (T _C =25°C) | 70 | W |
| TJ | Junction Temperature | 150 | °C |
| T _{STG} | Storage Temperature | - 65 ~ 150 | °C |



| Symbol | Parameter | Test Condition | Min. | Тур. | Max. | Units |
|------------------------|---|--|-----------------------|------|--------------------------|----------------|
| V _{CEO} (sus) | *Collector-Emitter Sustaining Voltage : BDX33 : BDX33A : BDX33B : BDX33C | I _C = 100mA I _B = 0 | 45 60 80 100 | | | V V V |
| V _{CER} (sus) | * Collector-Emitter Sustaining Voltage : BDX33 : BDX33A : BDX33B : BDX33C | $I_{C} = 100 \text{mA}, I_{B} = 0$ $R_{BE} = 100 \Omega$ | 45 60 80 100 | | | V V V |
| V _{CEV} (sus) | * Collector-Emitter Sustaining Voltage : BDX33 : BDX33A : BDX33B : BDX33C | I _C = 100mA, I _B = 0 V _{BE} = 1.5V | 45 60 80 100 | | | V V V |
| I _{CBO} | Collector Cut-off Current : BDX33 : BDX33A : BDX33B : BDX33C | $V_{CB} = 45V, I_{E} = 0$ $V_{CB} = 60V, I_{E} = 0$ $V_{CB} = 80V, I_{E} = 0$ $V_{CB} = 100V, I_{E} = 0$ | | | 0.2 0.2 0.2 0.2 | mA mA mA |
| I _{CEO} | Collector Cut-off Current : BDX33 : BDX33A : BDX33B : BDX33C | $V_{CE} = 22V, I_{B} = 0$ $V_{CE} = 30V, I_{B} = 0$ $V_{CE} = 40V, I_{B} = 0$ $V_{CE} = 50V, I_{B} = 0$ | | | 0.5 0.5 0.5 0.5 | mA mA mA |
| I _{EBO} | Emitter Cut-off Current | $V_{EB} = 5V, I_{C} = 0$ | | | 5 | mA |
| h _{FE} | * DC Current Gain : BDX33/34 : BDX33B/33C | $V_{CE} = 3V, I_{C} = 4A$ $V_{CE} = 3V, I_{C} = 3A$ | 750 750 | | | |
| V _{CE} (sat) | * Collector-Emitter Saturation Voltage : BDX33/33A : BDX33B/33C | $I_{C} = 4A, I_{B} = 8mA$ $I_{C} = 3A, I_{B} = 6mA$ | | | 2.5 2.5 | V V |
| V _{BE} (on) | * Base-Emitter ON Voltage : BDX33/33A : BDX33B/33C | V _{CE} = 3V, I _C = 4A V _{CE} = 3V, I _C = 3A | | | 2.5 2.5 | V V |
| V _F | * Parallel Diode Forward Voltage | I _F = 8A | | | 4 | V |

^{*} Pulse Test: PW=300µs, duty Cycle =1.5% Pulse

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Typical Characteristics

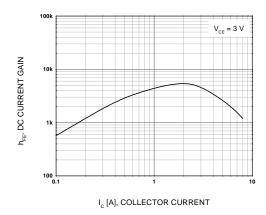


Figure 1. DC Current Gain

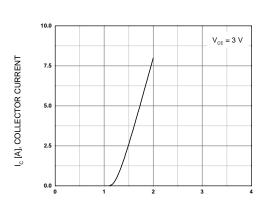


Figure 3. Base-Emitter On Voltage

 $V_{\rm BE}$ [V], BASE-EMITTER VOLTAGE

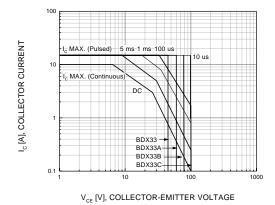


Figure 5. Safe Operating Area

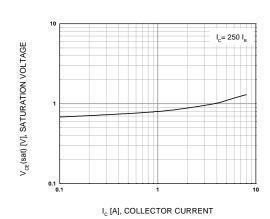


Figure 2. Collector-Emitter Saturation Voltage

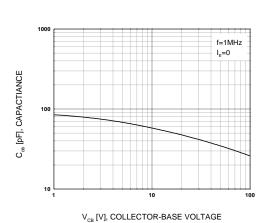


Figure 4. Output Capacitance

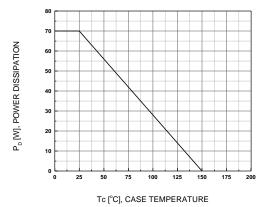
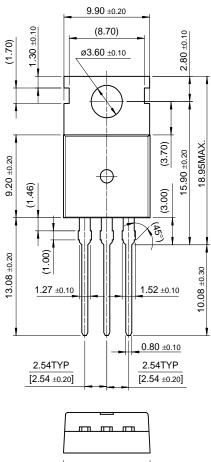


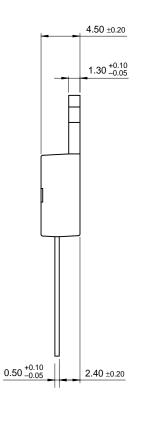
Figure 6. Power Derating

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Package Demensions

TO-220





10.00 ±0.20

Dimensions in Millimeters

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